

MOS INTEGRATED CIRCUIT μ PD23C128000L

128M-BIT MASK-PROGRAMMABLE ROM 16M-WORD BY 8-BIT (BYTE MODE) / 8M-WORD BY 16-BIT (WORD MODE)

Description

The μ PD23C128000L is a 134,217,728 bits mask-programmable ROM. The word organization is selectable (BYTE mode : 16,777,216 words by 8 bits, WORD mode : 8,388,608 words by 16 bits).

The active levels of OE (Output Enable Input) can be selected with mask-option.

The μ PD23C128000L is packed in 48-pin plastic TSOP(I).

Features

Word organization

16,777,216 words by 8 bits (BYTE mode)

8,388,608 words by 16 bits (WORD mode)

• Operating supply voltage: Vcc = 2.7 to 3.6 V

Operating supply voltage	Access time	Power supply current (Active mode)	Standby current (CMOS level input)
Vcc	ns (MAX.)	mA (MAX.)	μA (MAX.)
$3.3~\text{V}\pm0.3~\text{V}$	110	55	30
$3.0~\text{V}\pm0.3~\text{V}$	120	50	30

Ordering Information

Part Number	Package
μPD23C128000LGY-xxx-MJH	48-pin Plastic TSOP(I) (12 x 18) (Normal bent)
μPD23C128000LGY-xxx-MKH	48-pin Plastic TSOP(I) (12 x 18) (Reverse bent)

(xxx: ROM code suffix No.)

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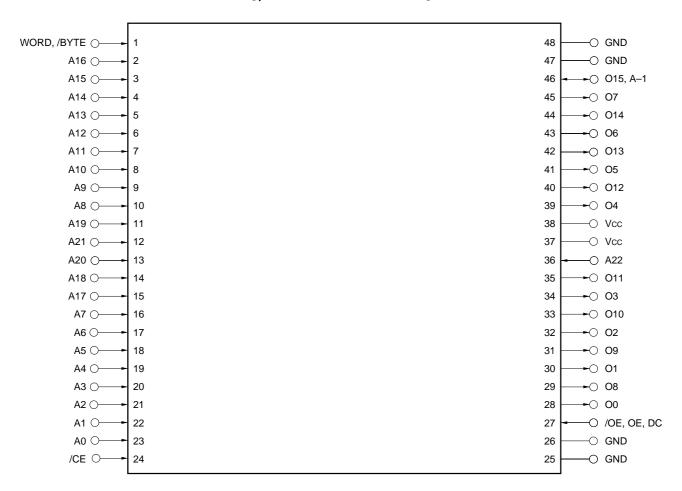
Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.



* Pin Configurations (Marking Side)

/xxx indicates active low signal.

48-pin plastic TSOP(I) (12 x 18) (Normal bent) [μ PD23C128000LGY-xxx-MJH]



A0 - A22 : Address inputs
O0 - O7, O8 - O14 : Data outputs

O15, A–1 : Data output 15 (WORD mode),

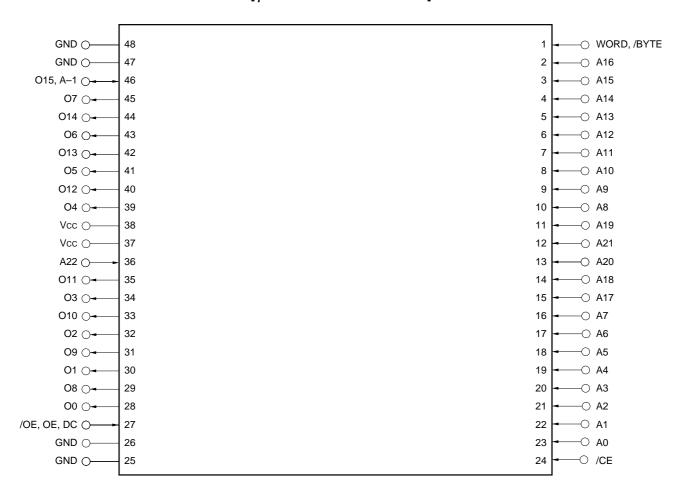
LSB Address input (BYTE mode)

WORD, /BYTE : Mode select
/CE : Chip Enable
/OE, OE : Output Enable
Vcc : Supply voltage

GND : Ground DC : Don't Care

Remark Refer to **Package Drawings** for the 1-pin index mark.

48-pin plastic TSOP(I) (12 x 18) (Reverse bent) [μ PD23C128000LGY-xxx-MKH]



A0 - A22 : Address inputs

O0 - O7, O8 - O14 : Data outputs

O15, A-1 : Data output 15 (WORD mode),

LSB Address input (BYTE mode)

WORD, /BYTE : Mode select
/CE : Chip Enable
/OE, OE : Output Enable
Vcc : Supply voltage

GND : Ground DC : Don't Care

Remark Refer to Package Drawings for the 1-pin index mark.

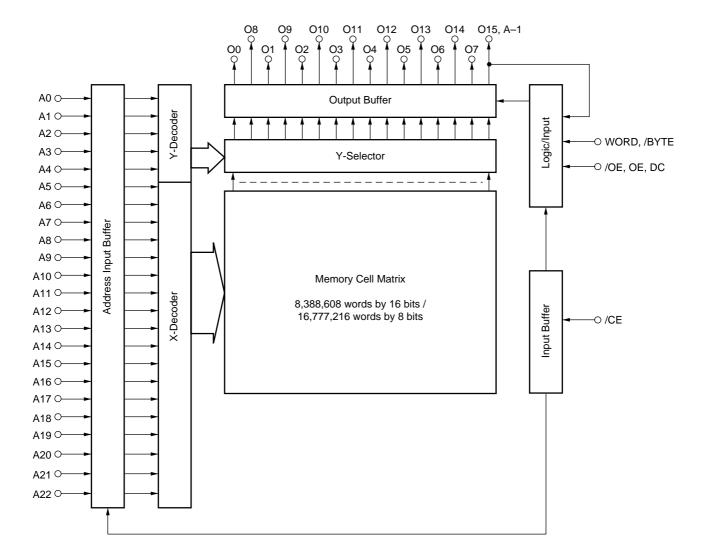


Input / Output Pin Functions

Pin name	Input / Output	Function			
WORD, /BYTE	Input	The pin for switching WORD mode and BYTE mode.			
		High level: WORD mode (8M-word by 16-bit)			
		Low level: BYTE mode (16M-word by 8-bit)			
A0 to A22	Input	Address input pins.			
(Address inputs)		A0 to A22 are used differently in the WORD mode and the BYTE mode.			
		WORD mode (8M-word by 16-bit)			
		A0 to A22 are used as 23 bits address signals.			
		BYTE mode (16M-word by 8-bit)			
		A0 to A22 are used as the upper 23 bits of total 24 bits of address signal.			
		(The least significant bit (A-1) is combined to O15.)			
O0 to O7, O8 to O14	Output	Data output pins.			
(Data outputs)		O0 to O7, O8 to O14 are used differently in the WORD mode and the BYTE mode.			
		WORD mode (8M-word by 16-bit)			
		The lower 15 bits of 16 bits data outputs to O0 to O14.			
		(The most significant bit (O15) combined to A-1.)			
		BYTE mode (16M-word by 8-bit)			
		8 bits data outputs to O0 to O7 and also O8 to O14 are high impedance.			
O15, A-1	Output, Input	O15, A-1 are used differently in the WORD mode and the BYTE mode.			
(Data output 15,		WORD mode (8M-word by 16-bit)			
LSB Address input)		The most significant output data bus (O15).			
		BYTE mode (16M-word by 8-bit)			
		The least significant address bus (A–1).			
/CE	Input	Chip activating signal.			
(Chip Enable)		When the OE is active, output states are following.			
		High level : High impedance			
		Low level : Data out			
/OE, OE, DC	Input	Output enable signal. The active level of OE is mask option. The active level of OE			
(Output Enable, Don't Care)		can be selected from high active, low active and Don't care at order.			
Vcc	-	Supply voltage			
GND	-	Ground			



Block Diagram





Mask Option

The active levels of output enable pin (/OE, OE, DC) are mask programmable and optional, and can be selected from among " 0 " " 1 " " x " shown in the table below.

Option	/OE, OE, DC	OE active level
0	/OE	L
1	OE	Н
х	DC	Don't care

Operation modes for each option are shown in the tables below.

Operation mode (Option: 0)

/CE	/OE	Mode	Output state		
L	L	Active Data out			
	Н		High impedance		
Н	H or L	Standby	High impedance		

Operation mode (Option: 1)

/CE	OE	Mode	Output state		
L	L	Active High impedan			
	Н		Data out		
Н	H or L	Standby	High impedance		

Operation mode (Option : x)

/CE	DC	Mode	Output state
L	H or L	Active	Data out
Н	H or L	Standby	High impedance

Remark L: Low level input

H: High level input



Electrical Specifications

Absolute Maximum Ratings

Parameter	Symbol	Condition	Rating	Unit	
Supply voltage	Vcc		-0.3 to +4.6	V	
Input voltage	Vı		-0.3 to Vcc+0.3		
Output voltage	Vo		-0.3 to Vcc+0.3	V	
Operating ambient temperature	TA		-10 to +70	°C	
Storage temperature	Tstg		-65 to +150	°C	

Caution Exposing the device to stress above those listed in Absolute Maximum Ratings could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational section of this specification. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

Capacitance (T_A = 25 °C)

Parameter	Symbol	Test condition	MIN.	TYP.	MAX.	Unit
Input capacitance	Сі	f = 1 MHz			10	pF
Output capacitance	Co				12	pF

DC Characteristics (TA = -10 to +70 °C, Vcc = 2.7 to 3.6 V)

Parameter	Symbol	Test cond	MIN.	TYP.	MAX.	Unit	
High level input voltage	VIH			2.2		Vcc + 0.3	V
Low level input voltage	VIL	$Vcc = 3.0 V \pm 0.3 V$		-0.3		+0.5	V
		$Vcc = 3.3 V \pm 0.3 V$		-0.3		+0.8	
High level output voltage	Vон	Io _H = -100 μA		2.4			V
Low level output voltage	Vol	IoL = 2.1 mA				0.4	V
Input leakage current	lu	Vi = 0 V to Vcc		-10		+10	μΑ
Output leakage current	ILO	Vo = 0 V to Vcc, Chip des	selected	-10		+10	μΑ
Power supply current	Icc1	/CE = V _I L (Active mode),	Vcc = 3.0 V ± 0.3 V			50	mA
		Io = 0 mA	Vcc = 3.3 V ± 0.3 V			55	
Standby current	Іссз	/CE = Vcc - 0.2 V (Stand			30	μΑ	



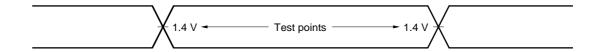
AC Characteristics (T_A = -10 to +70 °C, V_{CC} = 2.7 to 3.6 V)

Parameter	Symbol	Test condition	Vcc =	$Vcc = 3.0 V \pm 0.3 V$		Vcc = 3.3 V ± 0.3 V			Unit
			MIN.	TYP.	MAX.	MIN	TYP.	MAX.	
Address access time	tacc				120			110	ns
Chip enable access time	tce				120			110	ns
Output enable access time	t oe				40			30	ns
Output hold time	tон		0			0			ns
Output disable time	t DF		0		30	0		25	ns
WORD, /BYTE access time	t wB				120			110	ns

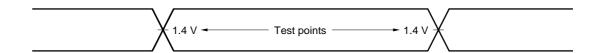
Remark to F is the time from inactivation of /CE or /OE, OE to high-impedance state output.

AC Test Conditions

Input waveform (Rise / Fall Time ≤ 5 ns)



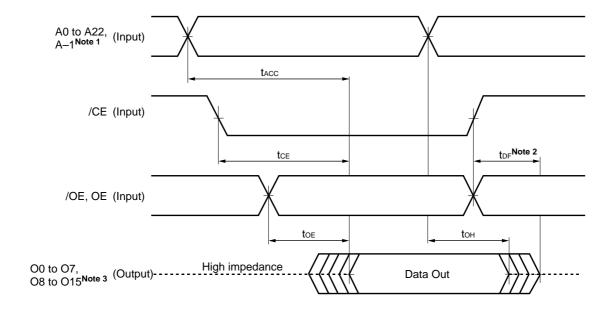
Output waveform



Output load

1TTL + 100 pF

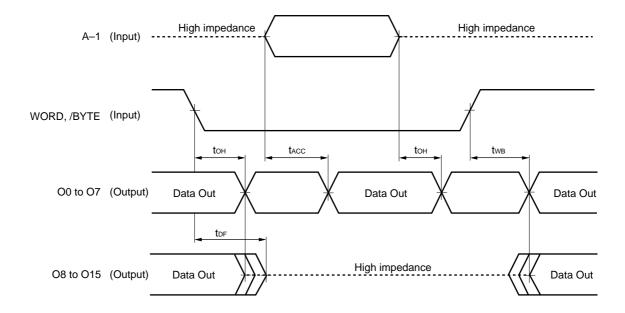
Read Cycle Timing Chart



Notes 1. During WORD mode, A-1 is O15.

- 2. tDF is specified when one of /CE, /OE, OE is inactivated.
- 3. During BYTE mode, O8 to O14 are high impedance and O15 is A-1.

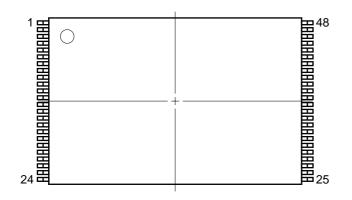
WORD, /BYTE Switch Timing Chart

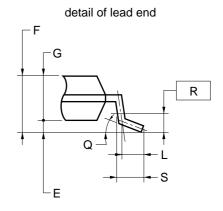


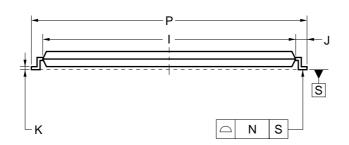
Remark /OE, OE and /CE : Active.

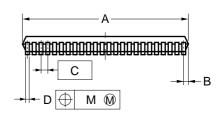
★ Package Drawings

48-PIN PLASTIC TSOP(I) (12x18)









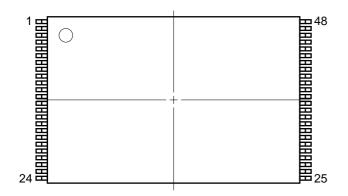
NOTES

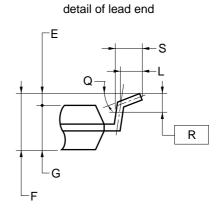
- Each lead centerline is located within 0.10 mm of its true position (T.P.) at maximum material condition.
- 2. "A" excludes mold flash. (Includes mold flash: 12.4 mm MAX.)

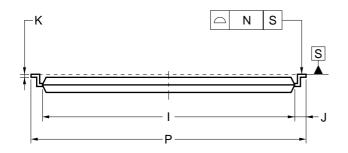
ITEM	MILLIMETERS
Α	12.0±0.1
В	0.45 MAX.
С	0.5 (T.P.)
D	0.22±0.05
Е	0.1±0.05
F	1.2 MAX.
G	1.0±0.05
I	16.4±0.1
J	0.8±0.2
K	0.145±0.05
L	0.5
М	0.10
N	0.10
Р	18.0±0.2
Q	3°+5°
R	0.25
S	0.60±0.15

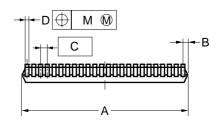
S48GY-50-MJH1-1

48-PIN PLASTIC TSOP(I) (12x18)









NOTES

- 1. Each lead centerline is located within 0.10 mm of its true position (T.P.) at maximum material condition.
- 2. "A" excludes mold flash. (Includes mold flash : 12.4 mm MAX.)

ITEM	MILLIMETERS
Α	12.0±0.1
В	0.45 MAX.
С	0.5 (T.P.)
D	0.22±0.05
Е	0.1±0.05
F	1.2 MAX.
G	1.0±0.05
I	16.4±0.1
J	0.8±0.2
K	0.145±0.05
L	0.5
М	0.10
N	0.10
Р	18.0±0.2
Q	3°+5° -3°
R	0.25
S	0.60±0.15
0.40.0V/ E0.10:::::::	

S48GY-50-MKH1-1



Recommended Soldering Conditions

Please consult with our sales offices for soldering conditions of the μ PD23C128000L.

Types of Surface Mount Device

 $\mu PD23C128000LGY-MJH: 48-pin plastic TSOP(I) \ (12 x 18) \ (Normal bent)$ $\mu PD23C128000LGY-MKH: 48-pin plastic TSOP(I) \ (12 x 18) \ (Reverse bent)$



[MEMO]



[MEMO]

NOTES FOR CMOS DEVICES -

1 PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note:

Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

(2) HANDLING OF UNUSED INPUT PINS FOR CMOS

Note

No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

(3) STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note:

Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

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 - "Standard", "Special", and "Specific". The Specific quality grade applies only to devices developed based on a customer designated "quality assurance program" for a specific application. The recommended applications of a device depend on its quality grade, as indicated below. Customers must check the quality grade of each device before using it in a particular application.
 - Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots
 - Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)
 - Specific: Aircraft, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

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